PROCESS CP761R

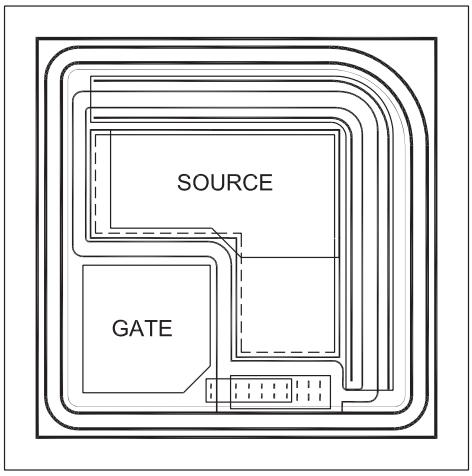
Small Signal MOSFET

P-Channel Enhancement-Mode MOSFET Chip

PROCESS DETAILS

Die Size	14.2 x 14.2 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	3.94 x 3.94 MILS
Source Bonding Pad Area	3.94 x 7.08 MILS
Top Side Metalization	Al-Si - 35,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE DRAIN R1

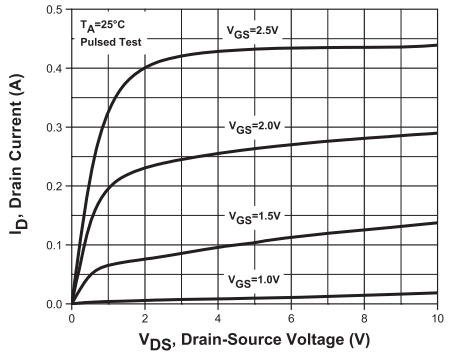
GROSS DIE PER 6 INCH WAFER
123,000

PRINCIPAL DEVICE TYPES
CEDM8001
CMNDM8001

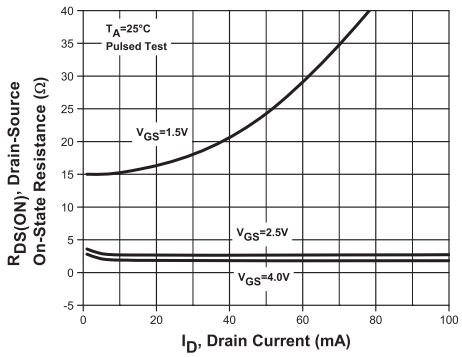
PROCESS CP761R

Typical Electrical Characteristics

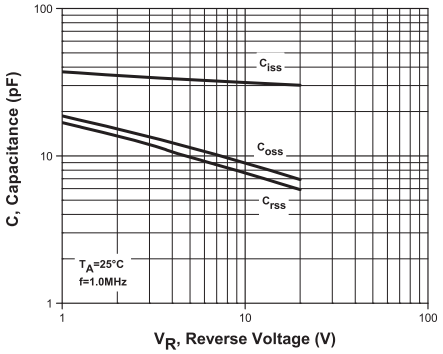
Output Characteristics



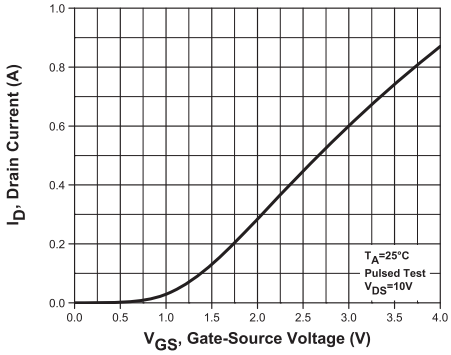
Drain Source On Resistance



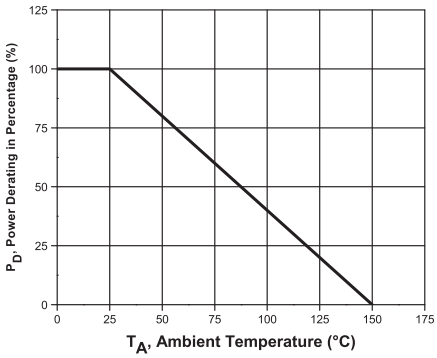
Capacitance



Transfer Characteristics



Normalized Power Derating



R1 (2-September 2010)